

# UF28100H



**RF Power MOSFET Transistor**  
**100W, 100-500 MHz, 28V**

**M/A-COM Products**  
**Released - Ver 08.07**

## Features

- N-channel enhancement mode device
- DMOS structure
- Lower capacitances for broadband operation
- High saturated output power
- Lower noise figure than competitive devices
- RoHS Compliant

## ABSOLUTE MAXIMUM RATINGS AT 25° C

Parameter	Symbol	Rating	Units
Drain-Source Voltage	$V_{DS}$	65	V
Gate-Source Voltage	$V_{GS}$	20	V
Drain-Source Current	$I_{DS}$	12*	A
Power Dissipation	$P_D$	250	W
Junction Temperature	$T_J$	200	°C
Storage Temperature	$T_{STG}$	-55 to +150	°C
Thermal Resistance	$\theta_{JC}$	0.7	°C/W

## TYPICAL DEVICE IMPEDANCES

F (MHz)	$Z_{IN}$ ( $\Omega$ )	$Z_{LOAD}$ ( $\Omega$ )
100	4.5-j6.0	14.5+j0.5
300	2.25-j1.75	7.5+j1.0
500	1.5+j5.5	3.5+j3.5

$V_{DD}=28V, I_{DQ}=600\text{ Ma}, P_{OUT}=100.0\text{ W}$

$Z_{IN}$  is the series equivalent input impedance of the device from gate to gate.

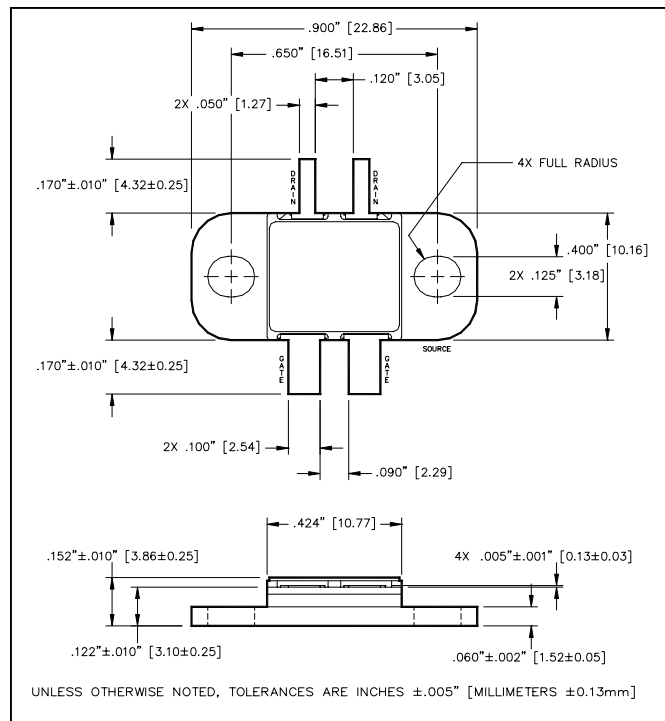
$Z_{LOAD}$  is the optimum series equivalent load impedance as measured from drain

## ELECTRICAL CHARACTERISTICS AT 25°C

Parameter	Symbol	Min	Max	Units	Test Conditions
Drain-Source Breakdown Voltage	$BV_{DSS}$	65	-	V	$V_{GS} = 0.0\text{ V}, I_{DS} = 15.0\text{ mA}$
Drain-Source Leakage Current	$I_{DSS}$	-	3.0	mA	$V_{GS} = 28.0\text{ V}, V_{DS} = 0.0\text{ V}$
Gate-Source Leakage Current	$I_{GSS}$	-	3.0	$\mu\text{A}$	$V_{GS} = 20.0\text{ V}, V_{DS} = 0.0\text{ V}$
Gate Threshold Voltage	$V_{GS(TH)}$	2.0	6.0	V	$V_{DS} = 10.0\text{ V}, I_{DS} = 300.0\text{ mA}$
Forward Transconductance	$G_M$	1.5	-	S	$V_{DS} = 10.0\text{ V}, I_{DS} = 3000.0\text{ mA}, \Delta V_{GS} = 1.0V, 80\ \mu\text{s Pulse}$
Input Capacitance	$C_{ISS}$	-	135	pF	$V_{DS} = 28.0\text{ V}, F = 1.0\text{ MHz}$
Output Capacitance	$C_{OSS}$	-	90	pF	$V_{DS} = 28.0\text{ V}, F = 1.0\text{ MHz}$
Reverse Capacitance	$C_{RSS}$	-	24	pF	$V_{DS} = 28.0\text{ V}, F = 1.0\text{ MHz}$
Power Gain	$G_P$	10	-	dB	$V_{DD} = 28.0\text{ V}, I_{DQ} = 600.0\text{ mA}, P_{OUT} = 100.0\text{ W } F = 500\text{ MHz}$
Drain Efficiency	$\eta_D$	50	-	%	$V_{DD} = 28.0\text{ V}, I_{DQ} = 600.0\text{ mA}, P_{OUT} = 100.0\text{ W } F = 500\text{ MHz}$
Return Loss	$R_L$	10	-	dB	$V_{DD} = 28.0\text{ V}, I_{DQ} = 600.0\text{ mA}, P_{OUT} = 100.0\text{ W } F = 500\text{ MHz}$
Load Mismatch Tolerance	VSWR-T	-	30:1	-	$V_{DD} = 28.0\text{ V}, I_{DQ} = 600.0\text{ mA}, P_{OUT} = 100.0\text{ W } F = 500\text{ MHz}$

\*Per side

## PACKAGE OUTLINE

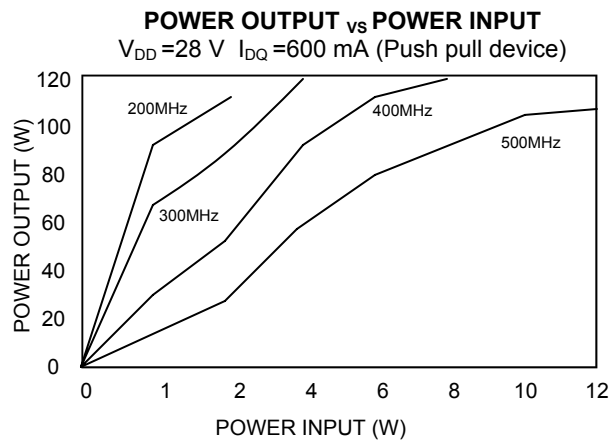
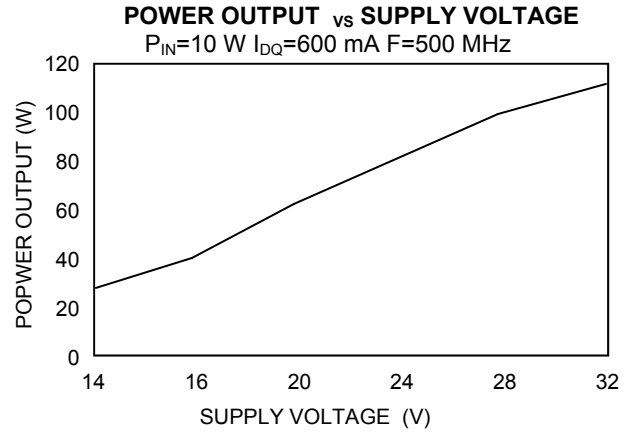
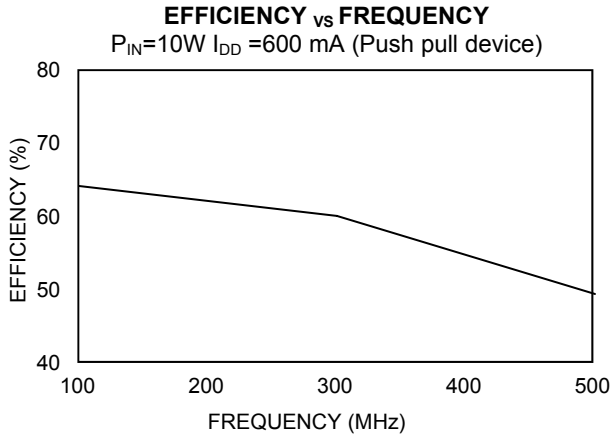


**ADVANCED:** Data Sheets contain information regarding a product M/A-COM Technology Solutions is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed.  
**PRELIMINARY:** Data Sheets contain information regarding a product M/A-COM Technology Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available. Commitment to produce in volume is not guaranteed.

- **North America** Tel: 800.366.2266 / Fax: 978.366.2266
  - **Europe** Tel: 44.1908.574.200 / Fax: 44.1908.574.300
  - **Asia/Pacific** Tel: 81.44.844.8296 / Fax: 81.44.844.8298
- Visit [www.macomtech.com](http://www.macomtech.com) for additional data sheets and product information.

M/A-COM Technology Solutions Inc. and its affiliates reserve the right to make changes to the product(s) or information contained herein without notice.

**Typical Broadband Performance Curves**

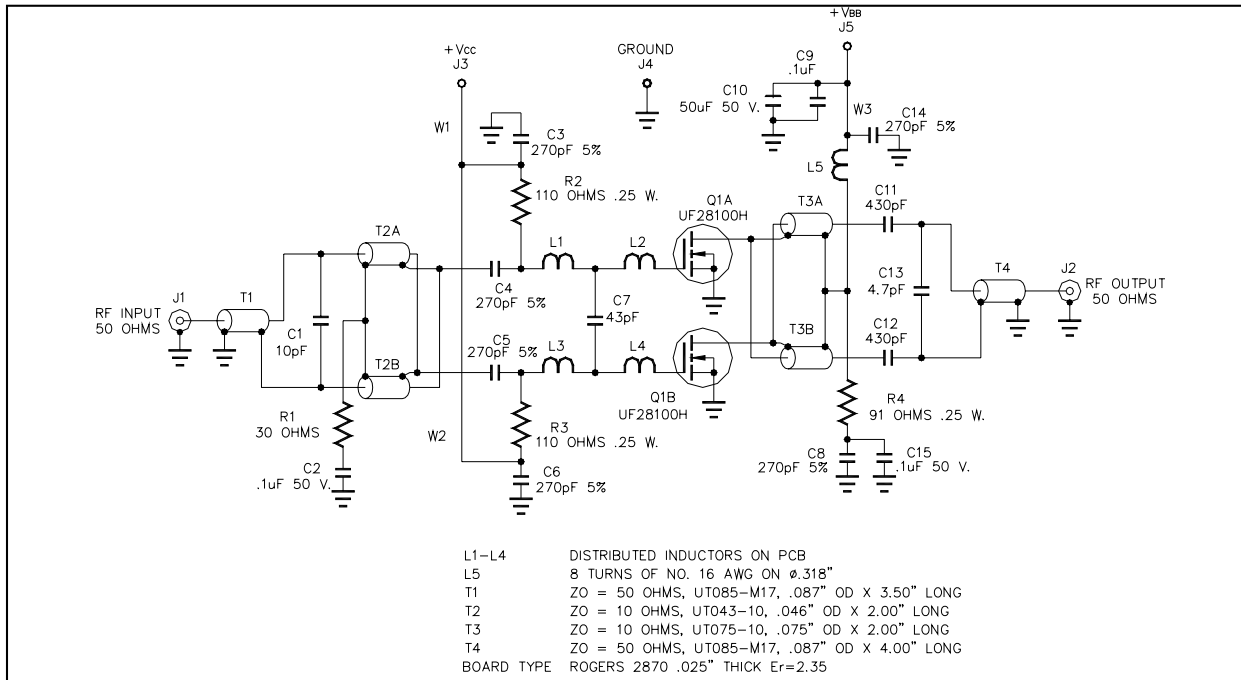


# UF28100H

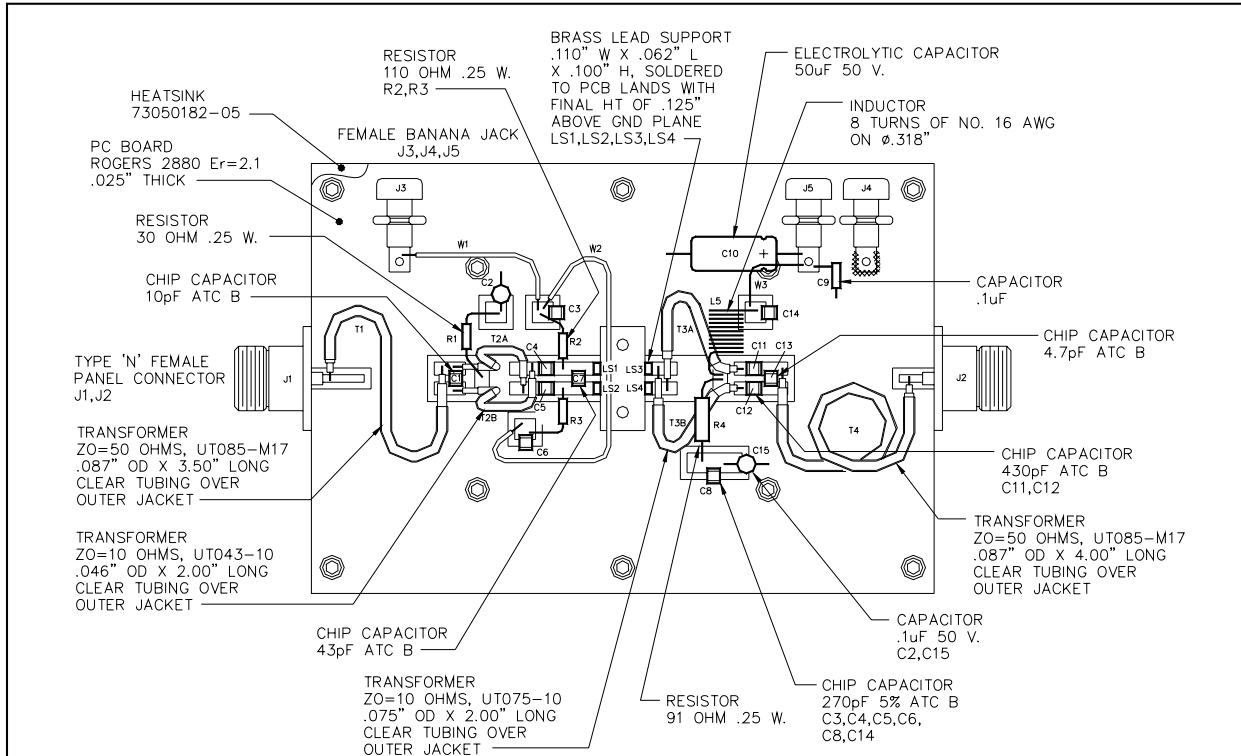
RF Power MOSFET Transistor  
100W, 100-500 MHz, 28V

M/A-COM Products  
Released - Ver 08.07

## TEST FIXTURE SCHEMATIC



## TEST FIXTURE ASSEMBLY



**ADVANCED:** Data Sheets contain information regarding a product M/A-COM Technology Solutions is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed.  
**PRELIMINARY:** Data Sheets contain information regarding a product M/A-COM Technology Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available. Commitment to produce in volume is not guaranteed.

- **North America** Tel: 800.366.2266 / Fax: 978.366.2266
- **Europe** Tel: 44.1908.574.200 / Fax: 44.1908.574.300
- **Asia/Pacific** Tel: 81.44.844.8296 / Fax: 81.44.844.8298

Visit [www.macomtech.com](http://www.macomtech.com) for additional data sheets and product information.

M/A-COM Technology Solutions Inc. and its affiliates reserve the right to make changes to the product(s) or information contained herein without notice.

## Данный компонент на территории Российской Федерации

### Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

### Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: [info@moschip.ru](mailto:info@moschip.ru)

Skype отдела продаж:

moschip.ru

moschip.ru\_4

moschip.ru\_6

moschip.ru\_9